

CPC05-SIC05-1200

Silicon Carbide Schottky Rectifier Die 5.0 Amp, 1200 Volt

The CPC05-SIC05-1200 Silicon Carbide Schottky die is optimized for high temperature applications. Parametrically, the device is energy efficient as a result of low total conduction losses and minimal changes to switching characteristics as a function of temperature.

FEATURES:

- Positive temperature coefficient
- · Low reverse leakage current
- Temperature independent switching characteristics
- High operating junction temperature
- Metalization suitable for standard die attach technologies
- Top metalization optimized for wire bonding

APPLICATIONS:

- Power inverters
- · Industrial motor drives
- Switch-mode power supplies
- · Power factor correction
- Over-current protection



BACKSIDE CATHODE R0

MECHANICAL SPECIFICATIONS:

| 54.3 x 76.8 MILS | | | | | | |
|----------------------------------|--|--|--|--|--|--|
| 5.9 MILS | | | | | | |
| 39.8 x 61.8 MILS | | | | | | |
| AI – 50,000Å | | | | | | |
| Ti/Ni/Ag – 1,000Å/2,000Å/10,000Å | | | | | | |
| 3.15 MILS | | | | | | |
| 6 INCHES | | | | | | |
| 5,353 | | | | | | |
| | | | | | | |

| MAXIMUM RATINGS: (T _A =25°C) | SYMBOL | | UNITS |
|---------------------------------------------|-----------------------------------|-------------|-------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| DC Blocking Voltage | V_{R} | 1200 | V |
| Continuous Forward Current | Ι _F | 5.0 | Α |
| Peak Forward Surge Current (tp=10ms) | I _{FSM} | 37.5 | Α |
| Operating and Storage Junction Temperature* | T _I , T _{eta} | -55 to +175 | °C |

^{*}Maximum junction temperature was determined via a TO-247 package type.

ELECTRICAL CHARACTERISTICS: (T_J=25°C unless otherwise noted)

| SYMBOL | TEST CONDITIONS | TYP | MAX | |
|---------|---------------------------------------------|-----|-----|--|
| I_R | V _R =1200V | 30 | 190 | |
| V_{F} | I _F =5.0A | 1.5 | 1.7 | |
| V_{F} | I _F =5.0A, T _J =175°C | 2.5 | 3.0 | |
| 0 - | \/_ =000\/ | 26 | | |

| V_{F} | I _F =5.0A, T _J =175°C | 2.5 | 3.0 | V |
|---------|---------------------------------------------|-----|-----|----|
| Q_{C} | V _R =800V | 26 | | nC |
| CJ | V_R =1.0 V , f=1.0 M Hz | 260 | | pF |
| C_J | V _R =400V, f=1.0MHz | 24 | | pF |
| CJ | V_R =800 V , f=1.0 M Hz | 19 | | pF |

R1 (22-July 2020)

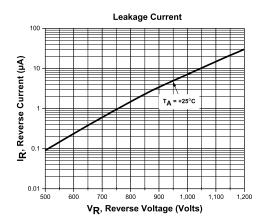
UNIT μΑ

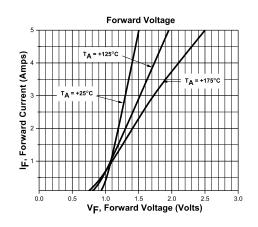
Theoretically, SiC die can operate at junction temperatures greater than 600°C.

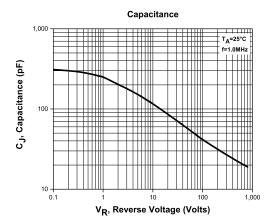
CPC05-SIC05-1200

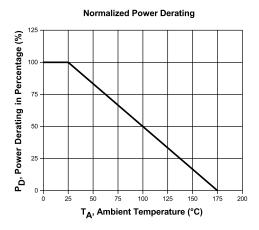
Typical Electrical Characteristics





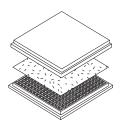






BARE DIE PACKING OPTIONS

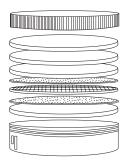




BARE DIE IN TRAY (WAFFLE) PACK

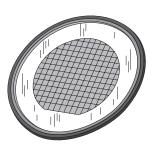
CT: Singulated die in tray (waffle) pack. (example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes). (example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked. (example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications: www.centralsemi.com/bdspecs

R2 (3-April 2017)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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